

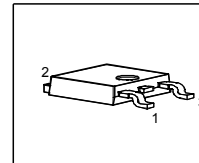
Cool MOS™ Power Transistor

Feature

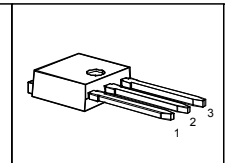
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance

V_{DS}	600	V
$R_{DS(on)}$	1.4	Ω
I_D	3.2	A

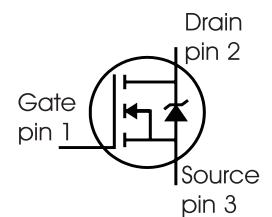
P-TO252.



P-TO251.



Type	Package	Ordering Code	Marking
SPU03N60S5	P-TO251.	Q67040-S4227	03N60S5
SPD03N60S5	P-TO252.	Q67040-S4187	03N60S5



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	I_D	3.2 2	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	5.7	
Avalanche energy, single pulse $I_D = 2.4\text{ A}$, $V_{DD} = 50\text{ V}$	E_{AS}	100	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹ $I_D = 3.2\text{ A}$, $V_{DD} = 50\text{ V}$	E_{AR}	0.2	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	3.2	A
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{ Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	P_{tot}	38	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480\text{ V}$, $I_D = 3.2\text{ A}$, $T_j = 125\text{ °C}$	dv/dt	20	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	3.3	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	75	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾	R_{thJA}	-	-	75 50	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j=25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$, $I_D=3.2\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=135\mu\text{A}$, $V_{GS}=V_{DS}$	3.5	4.5	5.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$, $T_j=25\text{ °C}$, $T_j=150\text{ °C}$	- -	0.5 -	1 70	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=2\text{A}$, $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	- -	1.26 3.4	1.4 -	Ω

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 2\text{A}$	-	1.8	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	420	-	pF
Output capacitance	C_{oss}		-	150	-	
Reverse transfer capacitance	C_{rss}		-	3.6	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 3.2\text{A}$, $R_G = 20\Omega$	-	35	-	ns
Rise time	t_r		-	25	-	
Turn-off delay time	$t_{d(off)}$		-	40	-	
Fall time	t_f		-	15	22.5	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$	-	3.5	-	nC
Gate to drain charge	Q_{gd}		-	7	-	
Gate charge total	Q_g	$V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$, $V_{GS} = 0\text{ to }10\text{V}$	-	12.4	16	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$	-	8	-	V

¹ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

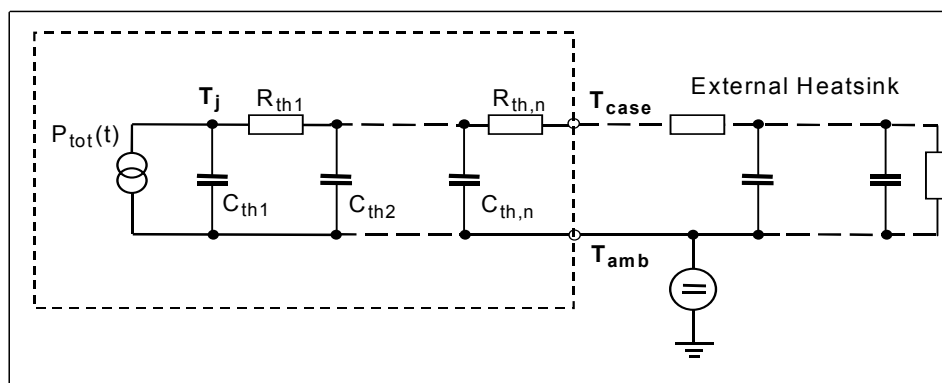
² Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C=25^\circ\text{C}$	-	-	3.2	A
Inverse diode direct current, pulsed	I_{SM}		-	-	5.7	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=350\text{V}, I_F=I_S,$	-	1000	1700	ns
Reverse recovery charge	Q_{rr}	$di_F/dt=100\text{A}/\mu\text{s}$	-	2.3	-	μC

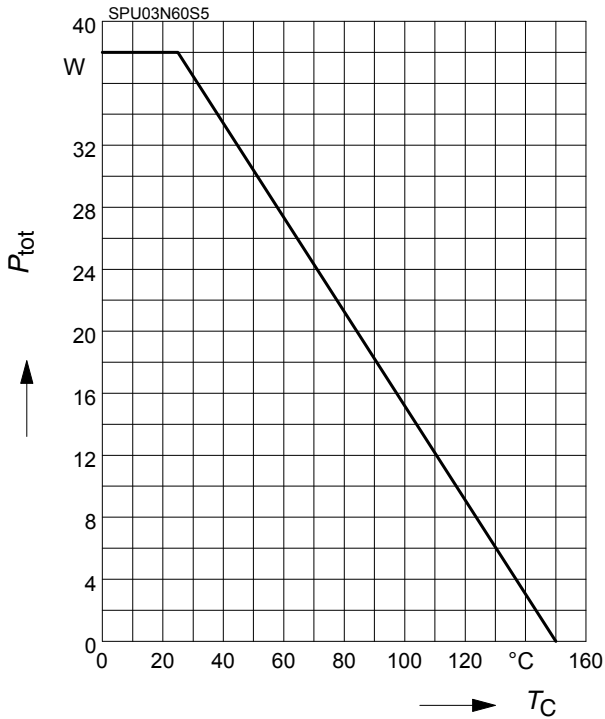
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.054	K/W	C_{th1}	0.00005232	Ws/K
R_{th2}	0.103		C_{th2}	0.0002034	
R_{th3}	0.178		C_{th3}	0.0002963	
R_{th4}	0.757		C_{th4}	0.0009103	
R_{th5}	0.682		C_{th5}	0.002084	
R_{th6}	0.202		C_{th6}	0.024	



1 Power dissipation

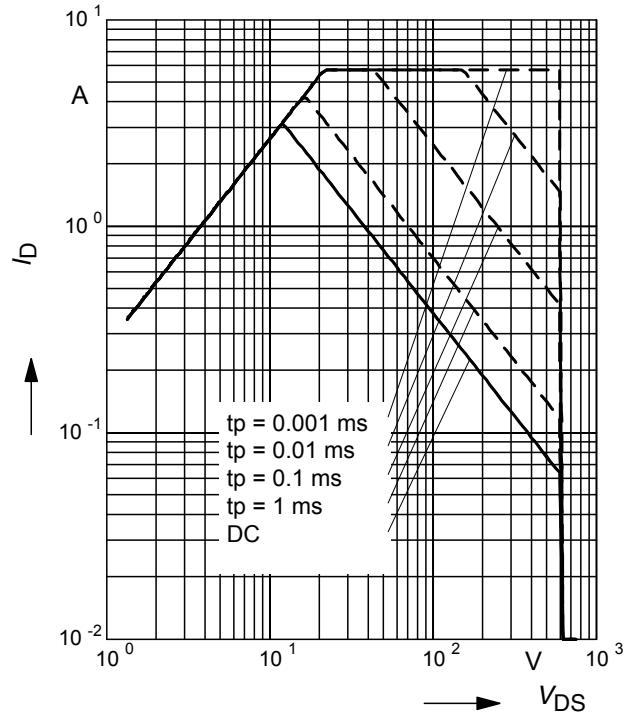
$P_{tot} = f(T_C)$



2 Safe operating area

$I_D = f(V_{DS})$

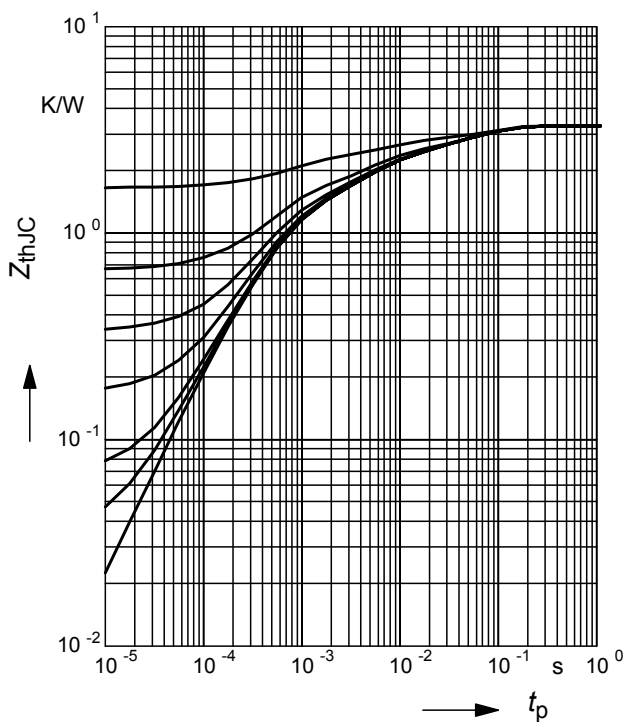
parameter : $D = 0$, $T_C = 25^\circ C$



3 Transient thermal impedance

$Z_{thJC} = f(t_p)$

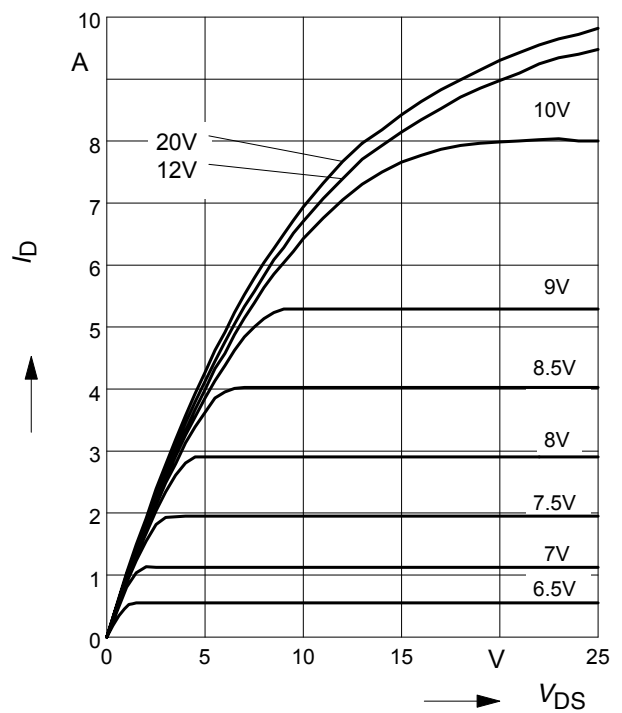
parameter: $D = t_p/T$



4 Typ. output characteristic

$I_D = f(V_{DS})$; $T_j = 25^\circ C$

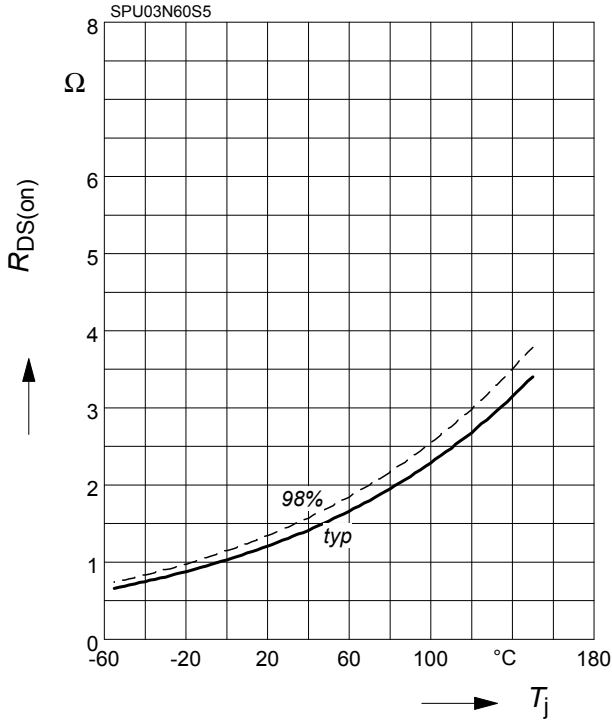
parameter: $t_p = 10 \mu s$, V_{GS}



5 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

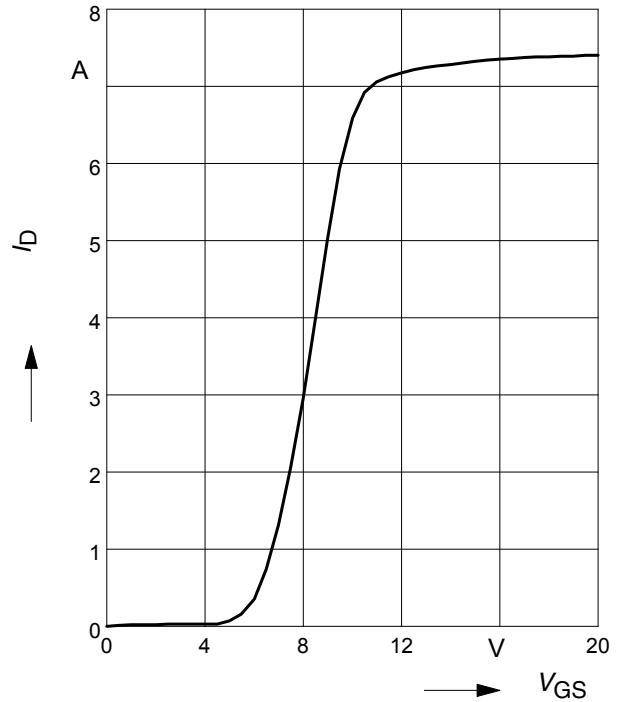
parameter: $I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$



6 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

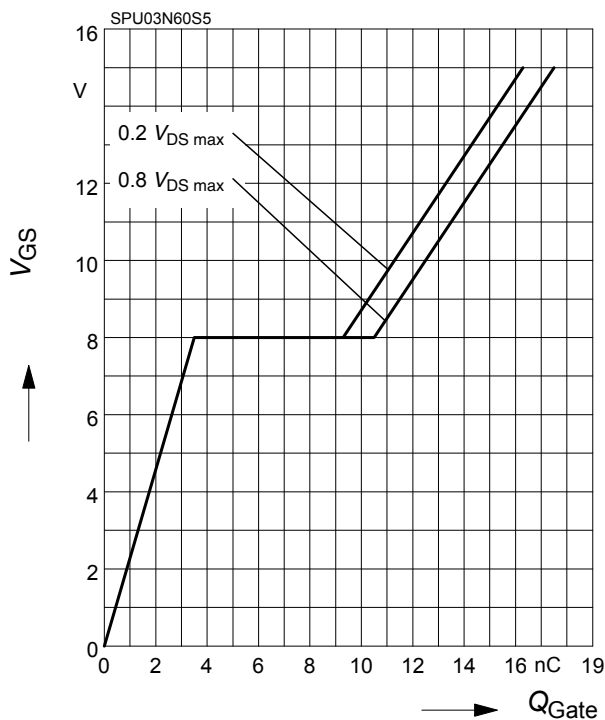
parameter: $t_p = 10 \mu\text{s}$



7 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

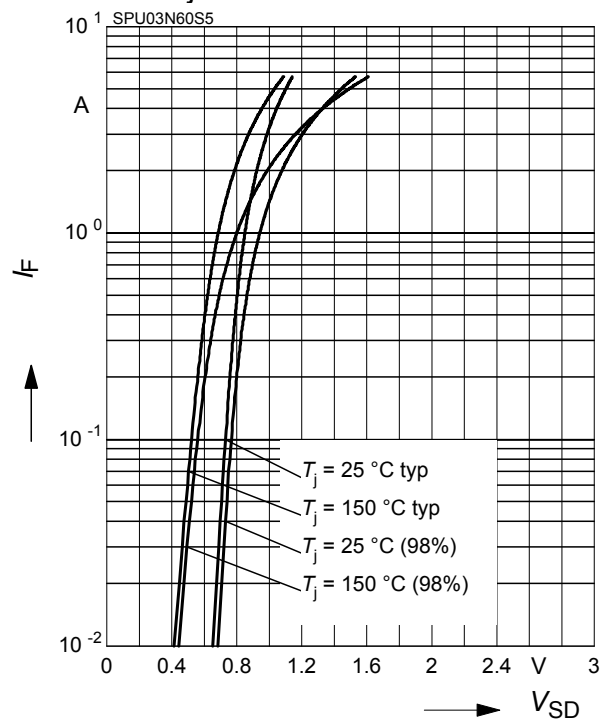
parameter: $I_D = 3.2 \text{ A pulsed}$



8 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

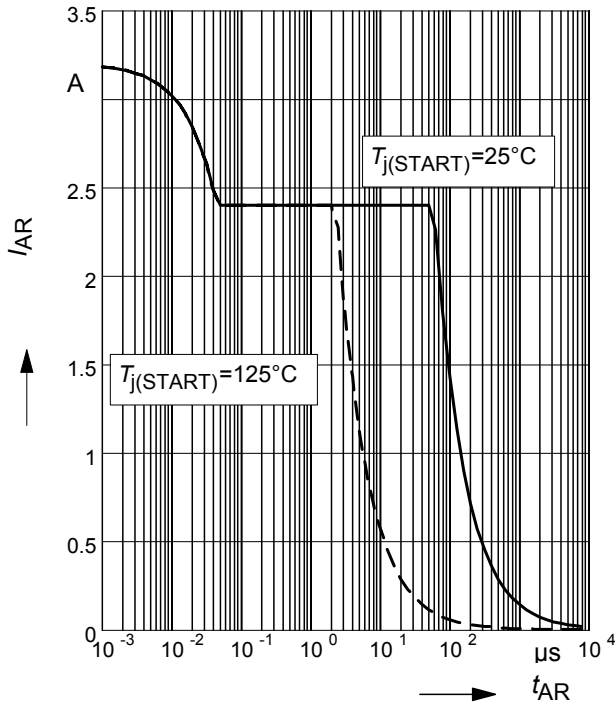
parameter: T_j , $t_p = 10 \mu\text{s}$



9 Avalanche SOA

$I_{AR} = f(t_{AR})$

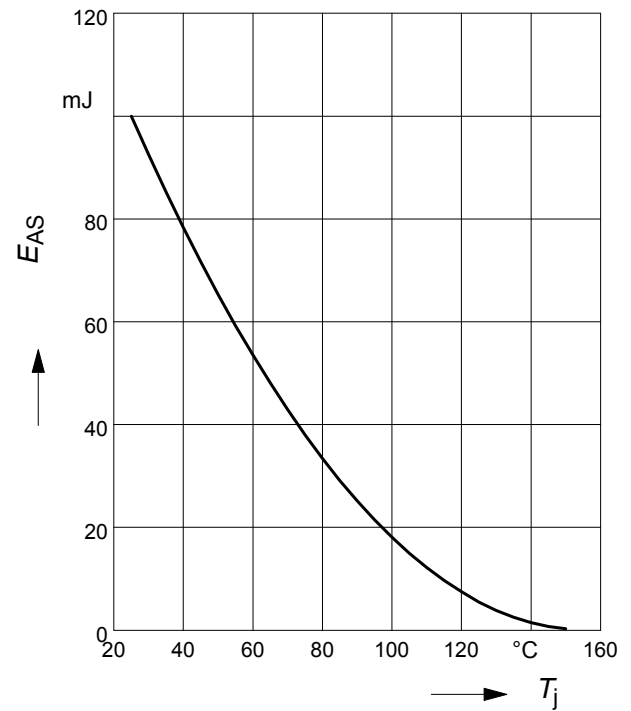
par.: $T_j \leq 150\text{ }^\circ\text{C}$



10 Avalanche energy

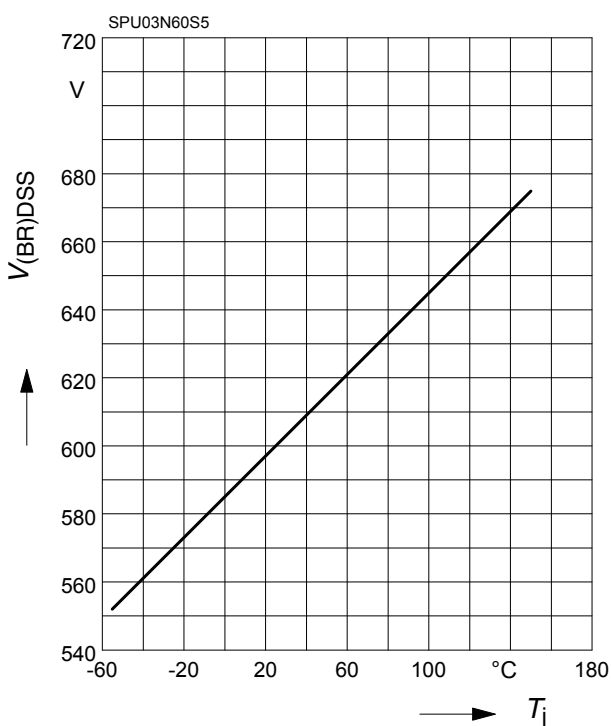
$E_{AS} = f(T_j)$

par.: $I_D = 2.4\text{ A}$, $V_{DD} = 50\text{ V}$



11 Drain-source breakdown voltage

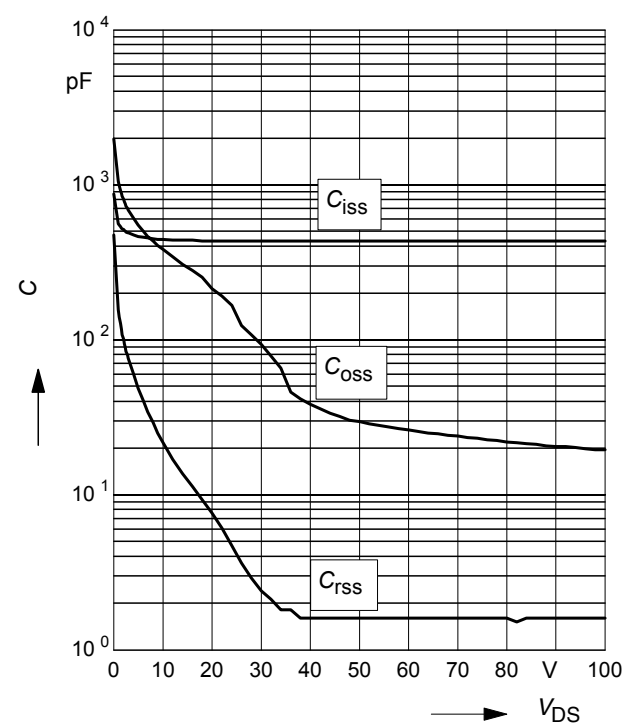
$V_{(BR)DSS} = f(T_j)$



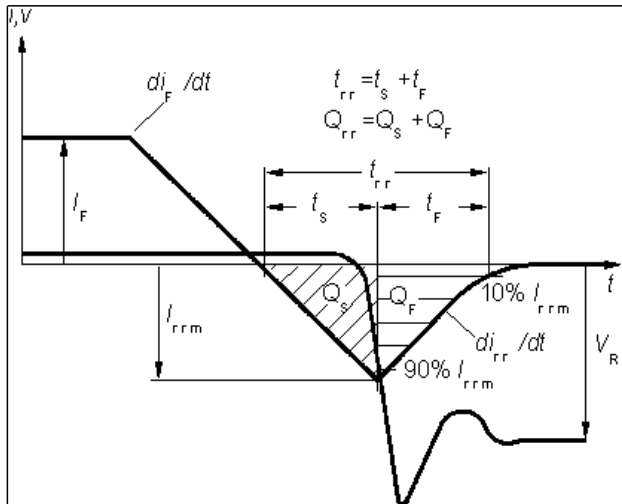
12 Typ. capacitances

$C = f(V_{DS})$

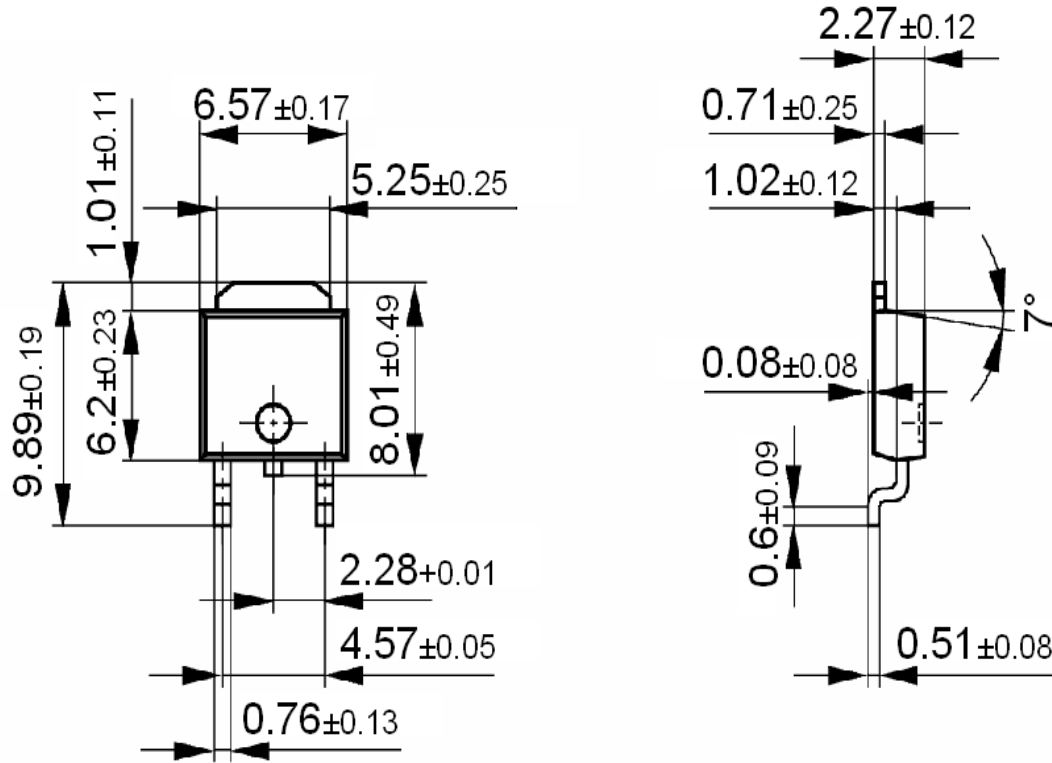
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



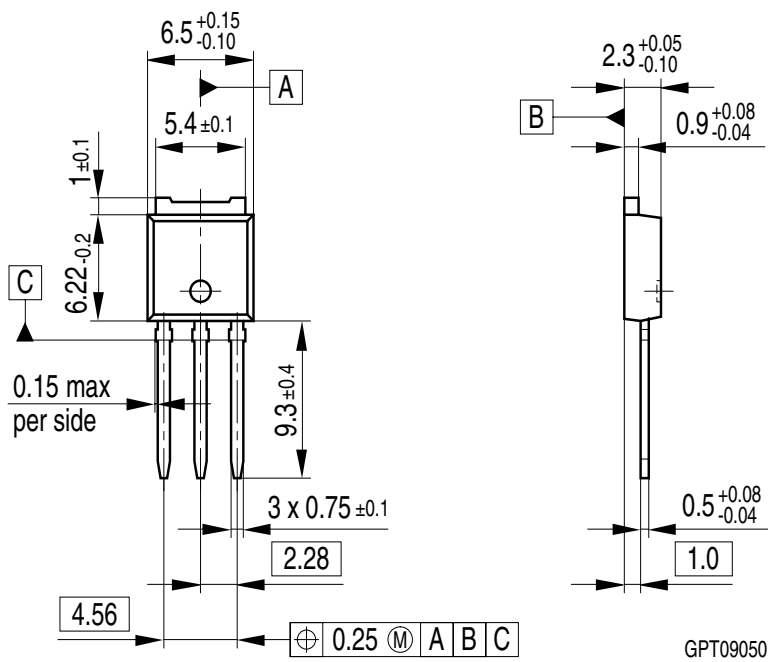
Definition of diodes switching characteristics



P-TO-252-3-1 (D-PAK)



P-TO-251-3-1 (I-PAK)



All metal surfaces tin plated, except area of cut.

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